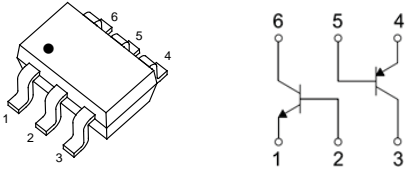


DUAL TRANSISTOR (NPN+PNP)	SOT-363 Plastic-Encapsulate Transistors
<p style="text-align: center;"><u>SOT-363</u></p>  <p style="text-align: center;">Marking :KNM</p>	<p>Features</p> <ul style="list-style-type: none"> • Epitaxial Planar Die Construction • Ideal for low Power Amplification and Switching • One 5551(NPN), one 5401(PNP)

MAXIMUM RATINGS NPN 5551 (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector- Base Voltage	180	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	0.2	A
P _C	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance, Junction to Ambient	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS NPN 5551 (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	180			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	160			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =120V, I _E =0			0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.05	μA
DC current gain	h _{FE1}	V _{CE} =5V, I _C =1mA	80			
	h _{FE2}	V _{CE} =5V, I _C =10mA	100		300	
	h _{FE3}	V _{CE} =5V, I _C =50mA	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA			0.15	V
		I _C =50mA, I _B =5mA			0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =10mA, I _B =1mA			1	V
		I _C =50mA, I _B =5mA			1	V
Output Capacitance	C _{obo}	V _{CB} = 10V, f = 1.0MHz, I _E = 0			6.0	pF
Current Gain-Bandwidth Product	f _T	V _{CE} = 10V, I _C = 10mA, f = 100MHz	100		300	MHz
Noise Figure	NF	V _{CE} = 5.0V, I _C = 200μA, R _S = 1.0kΩ, f = 1.0kHz			8.0	dB

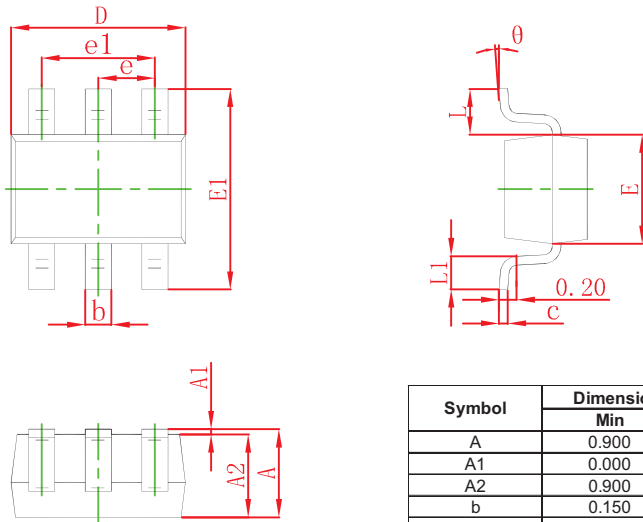
MAXIMUM RATINGS PNP 5401 (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector- Base Voltage	-160	V
V _{CE0}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance, Junction to Ambient	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS PNP 5401 (T_a=25°C unless otherwise specified)

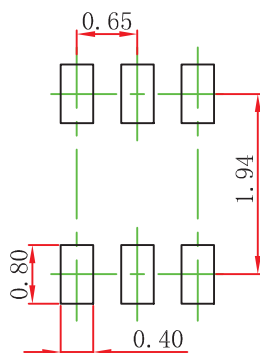
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-120V, I _E =0			-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V, I _C =0			-50	nA
DC current gain	h _{FE1}	V _{CE} =-5V, I _C =-1mA	50			
	h _{FE2}	V _{CE} =-5V, I _C =-10mA	100		300	
	h _{FE3}	V _{CE} =-5V, I _C =-50mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-1mA			-0.2	V
		I _C =-50mA, I _B =-5mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-10mA, I _B =-1mA			-1	V
		I _C =-50mA, I _B =-5mA			-1	V
Output Capacitance	C _{obo}	V _{CB} =-10V, f = 1.0MHz, I _E = 0			6.0	pF
Current Gain-Bandwidth Product	f _T	V _{CE} =-10V, I _C =-10mA, f = 100MHz	100		300	MHz
Noise Figure	NF	V _{CE} =-5.0V, I _C =-200μA, R _S = 10 Ω, f = 1.0kHz			8.0	dB

SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)